

NTMS5P02, NVMS5P02

MOSFET – Power, Single, P-Channel, Enhancement Mode, SOIC-8

-5.4 A, -20 V

Features

- High Density Power MOSFET with Ultra Low $R_{DS(on)}$ Providing Higher Efficiency
- Miniature SOIC-8 Surface Mount Package – Saves Board Space
- Diode Exhibits High Speed with Soft Recovery
- I_{DSS} Specified at Elevated Temperature
- Drain-to-Source Avalanche Energy Specified
- Mounting Information for the SOIC-8 Package is Provided
- These Devices are Pb-Free and are RoHS Compliant
- NVMS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Computers, Printers, PCMCIA Cards, Cellular & Cordless Telephones

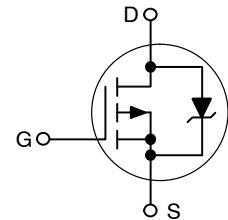


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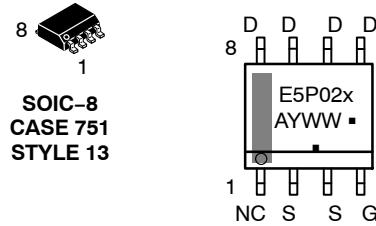
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V_{DSS}	$R_{DS(ON)}\text{ TYP}$	$I_D\text{ MAX}$
-20 V	26 m Ω @ -4.5 V	-5.4 A

Single P-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



E5P02 = Specific Device Code
x = Blank or S
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NTMS5P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NVMS5P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

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MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	-20	V
Drain-to-Gate Voltage (R _{GS} = 1.0 mΩ)	V _{DGR}	-20	V
Gate-to-Source Voltage – Continuous	V _{GS}	±10	V
Thermal Resistance – Junction-to-Ambient (Note 1) Total Power Dissipation @ T _A = 25°C Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	R _{θJA} P _D I _D I _D P _D I _D I _{DM}	50 2.5 -7.05 -5.62 1.2 -4.85 -28	°C/W W A A W A A
Thermal Resistance – Junction-to-Ambient (Note 2) Total Power Dissipation @ T _A = 25°C Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	R _{θJA} P _D I _D I _D P _D I _D I _{DM}	85 1.47 -5.40 -4.30 0.7 -3.72 -20	°C/W W A A W A A
Thermal Resistance – Junction-to-Ambient (Note 3) Total Power Dissipation @ T _A = 25°C Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	R _{θJA} P _D I _D I _D P _D I _D I _{DM}	159 0.79 -3.95 -3.15 0.38 -2.75 -12	°C/W W A A W A A
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Single Pulse Drain-to-Source Avalanche Energy – Starting T _J = 25°C (V _{DD} = -20 Vdc, V _{GS} = -5.0 Vdc, Peak I _L = -8.5 Apk, L = 10 mH, R _G = 25 Ω)	E _{AS}	360	mJ
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), t ≤ 10 seconds.
2. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), t = steady state.
3. Minimum FR-4 or G-10 PCB, t = Steady State.
4. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 5)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Breakdown Voltage ($V_{GS} = 0 \text{ Vdc}$, $I_D = -250 \mu\text{Adc}$) Temperature Coefficient (Positive)	$V_{(\text{BR})\text{DSS}}$	-20 -	-15	-	Vdc mV°C
Zero Gate Voltage Drain Current ($V_{DS} = -16 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$, $T_J = 25^\circ\text{C}$) ($V_{DS} = -16 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$, $T_J = 125^\circ\text{C}$) ($V_{DS} = -20 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$, $T_J = 25^\circ\text{C}$)	I_{DSS}	- - -	- - -0.2	-1.0 -10 -	μAdc
Gate-Body Leakage Current ($V_{GS} = -10 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$)	I_{GSS}	-	-	-100	nAdc
Gate-Body Leakage Current ($V_{GS} = +10 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$)	I_{GSS}	-	-	100	nAdc

ON CHARACTERISTICS

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = -250 \mu\text{Adc}$) Temperature Coefficient (Negative)	$V_{GS(\text{th})}$	-0.65 -	-0.9 2.9	-1.25 -	Vdc mV°C
Static Drain-to-Source On-State Resistance ($V_{GS} = -4.5 \text{ Vdc}$, $I_D = -5.4 \text{ Adc}$) ($V_{GS} = -2.5 \text{ Vdc}$, $I_D = -2.7 \text{ Adc}$)	$R_{\text{DS}(\text{on})}$	- -	0.026 0.037	0.033 0.048	Ω
Forward Transconductance ($V_{DS} = -9.0 \text{ Vdc}$, $I_D = -5.4 \text{ Adc}$)	g_{FS}	-	15	-	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = -16 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$	C_{iss}	-	1375	1900	pF
Output Capacitance		C_{oss}	-	510	900	
Reverse Transfer Capacitance		C_{rss}	-	200	380	

SWITCHING CHARACTERISTICS (Notes 6 & 7)

Turn-On Delay Time	$(V_{DD} = -16 \text{ Vdc}, I_D = -1.0 \text{ Adc}, V_{GS} = -4.5 \text{ Vdc}, R_G = 6.0 \Omega)$	$t_{\text{d}(\text{on})}$	-	18	35	ns
Rise Time		t_r	-	25	50	
Turn-Off Delay Time		$t_{\text{d}(\text{off})}$	-	70	125	
Fall Time		t_f	-	55	100	
Turn-On Delay Time	$(V_{DD} = -16 \text{ Vdc}, I_D = -5.4 \text{ Adc}, V_{GS} = -4.5 \text{ Vdc}, R_G = 6.0 \Omega)$	$t_{\text{d}(\text{on})}$	-	22	-	ns
Rise Time		t_r	-	70	-	
Turn-Off Delay Time		$t_{\text{d}(\text{off})}$	-	65	-	
Fall Time		t_f	-	90	-	
Total Gate Charge	$(V_{DS} = -16 \text{ Vdc}, V_{GS} = -4.5 \text{ Vdc}, I_D = -5.4 \text{ Adc})$	Q_{tot}	-	20	35	nC
Gate-Source Charge		Q_{gs}	-	4.0	-	
Gate-Drain Charge		Q_{gd}	-	7.0	-	

BODY-DRAIN DIODE RATINGS (Note 6)

Diode Forward On-Voltage	$(I_S = -5.4 \text{ Adc}, V_{GS} = 0 \text{ V})$ $(I_S = -5.4 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^\circ\text{C})$	V_{SD}	- -	-0.95 -0.72	-1.25 -	Vdc
Reverse Recovery Time	$(I_S = -5.4 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, dI_S/dt = 100 \text{ A}/\mu\text{s})$	t_{rr}	-	40	75	ns
		t_a	-	20	-	
		t_b	-	20	-	
Reverse Recovery Stored Charge		Q_{RR}	-	0.03	-	μC

5. Handling precautions to protect against electrostatic discharge is mandatory.

6. Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.

7. Switching characteristics are independent of operating junction temperature.

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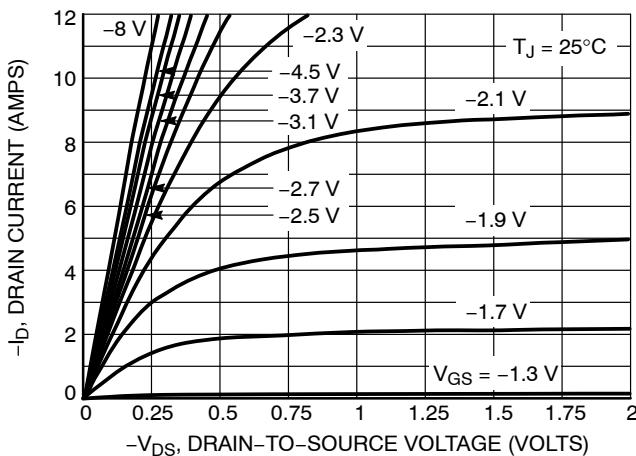


Figure 1. On-Region Characteristics

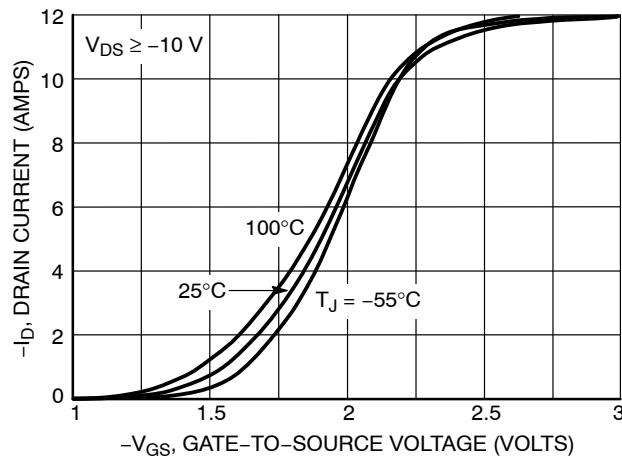


Figure 2. Transfer Characteristics

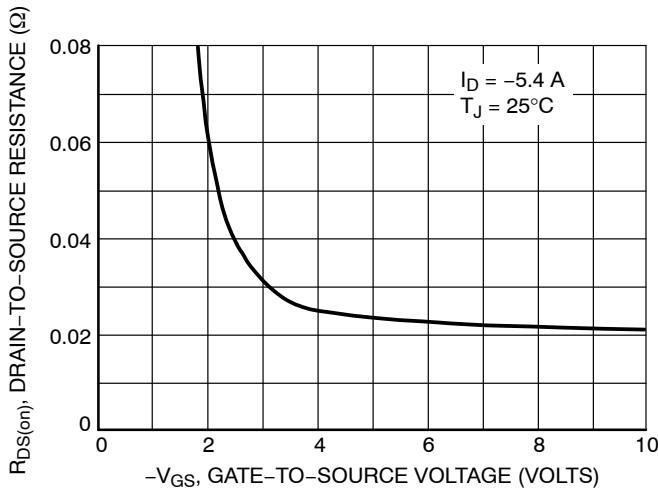


Figure 3. On-Resistance versus Gate-to-Source Voltage

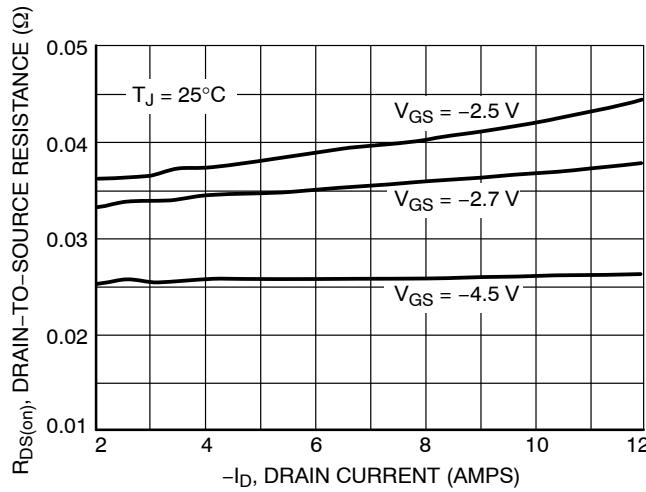


Figure 4. On-Resistance versus Drain Current and Gate Voltage

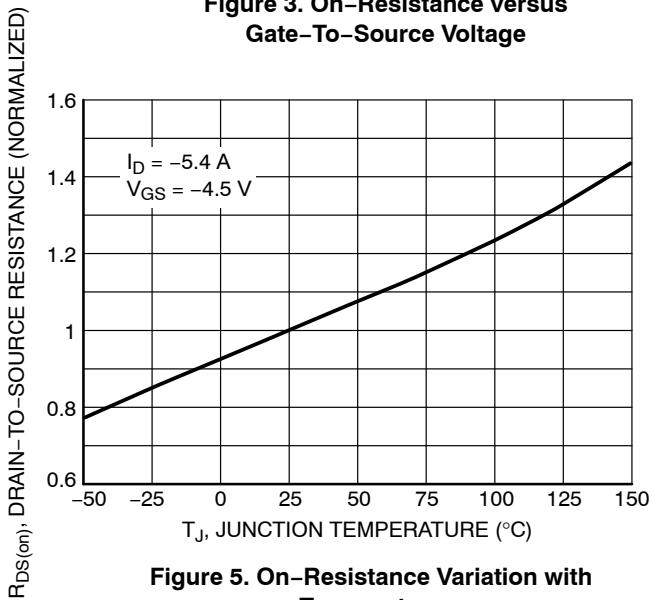


Figure 5. On-Resistance Variation with Temperature

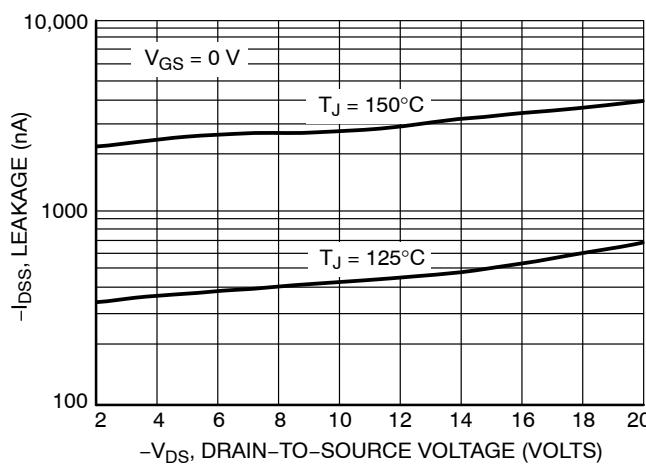


Figure 6. Drain-to-Source Leakage Current versus Voltage

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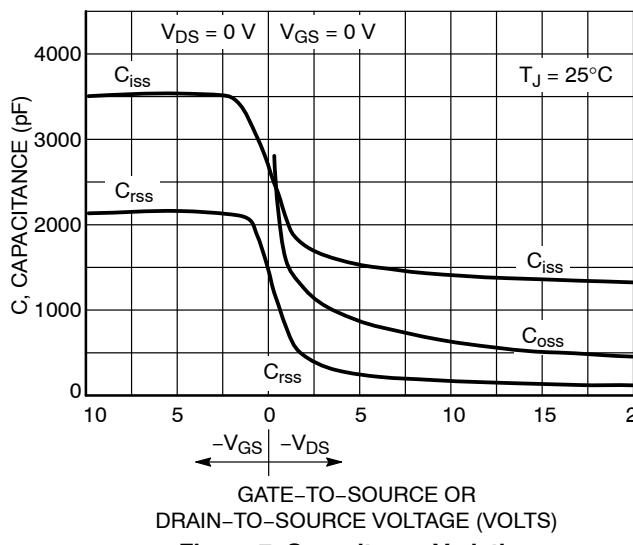


Figure 7. Capacitance Variation

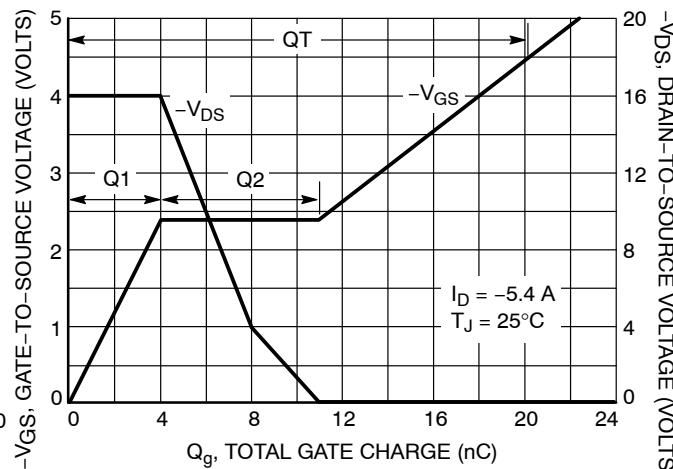


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

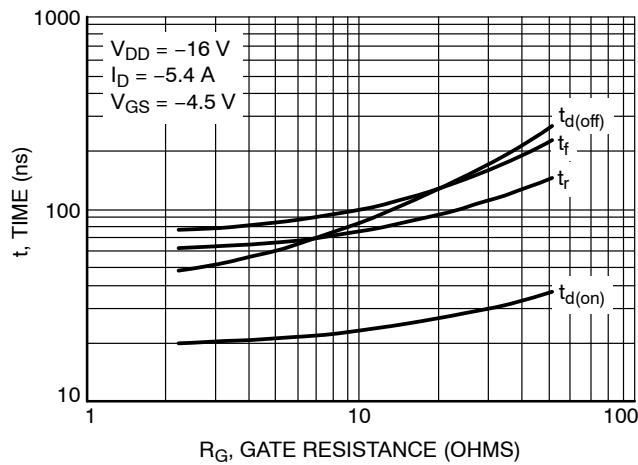


Figure 9. Resistive Switching Time Variation versus Gate Resistance

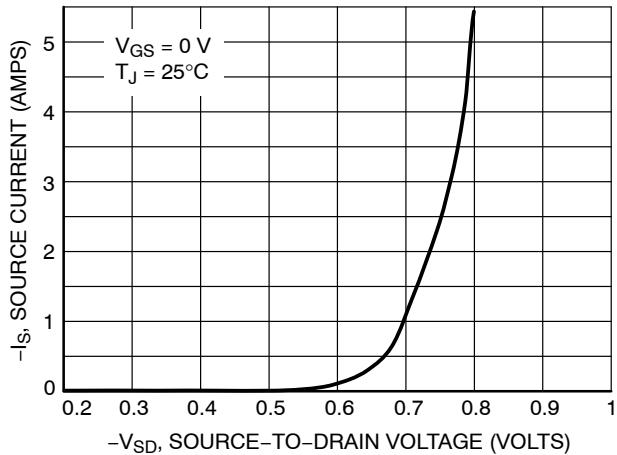


Figure 10. Diode Forward Voltage versus Current

DRAIN-TO-SOURCE DIODE CHARACTERISTICS

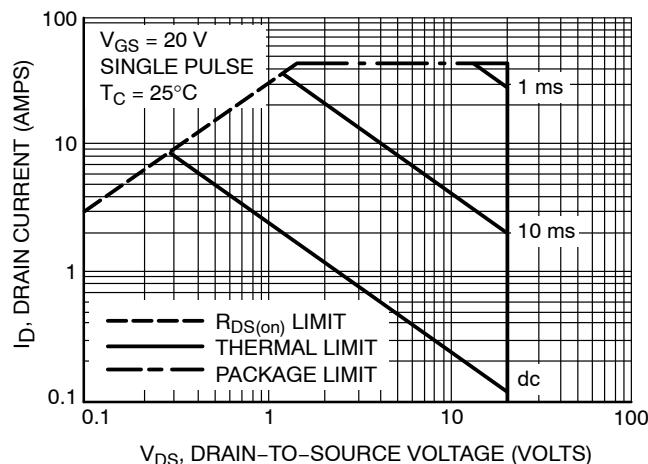


Figure 11. Maximum Rated Forward Biased Safe Operating Area

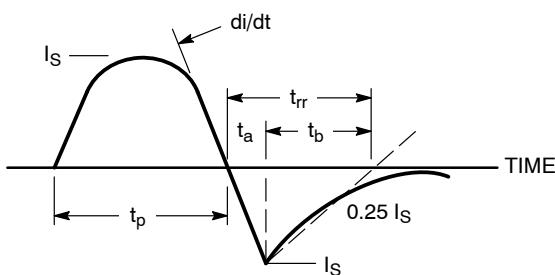


Figure 12. Diode Reverse Recovery Waveform

TYPICAL ELECTRICAL CHARACTERISTICS

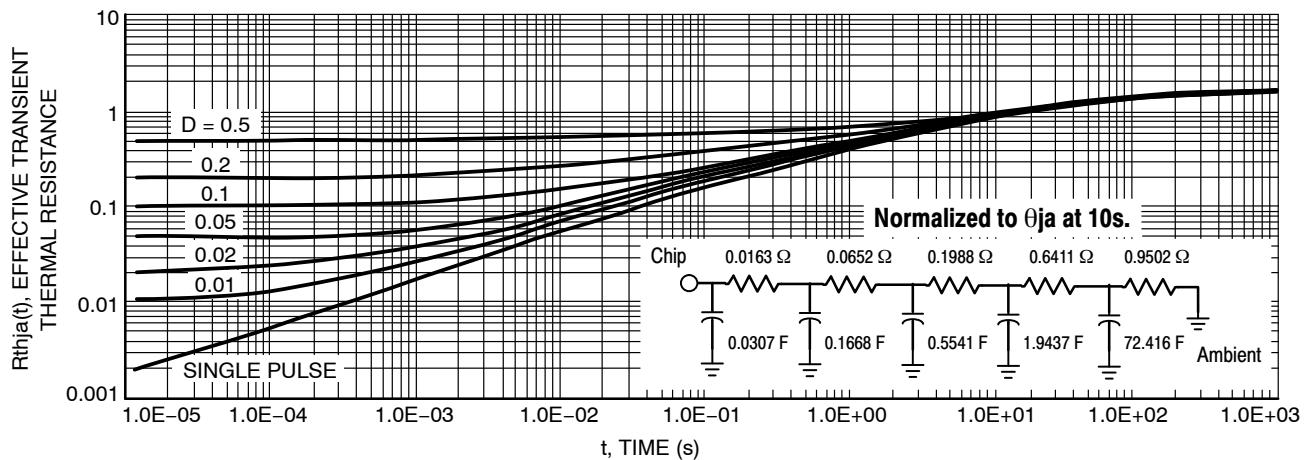


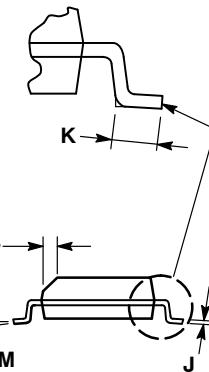
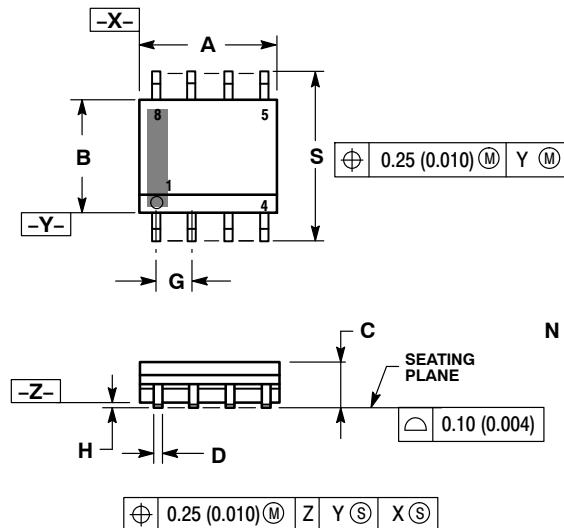
Figure 13. Thermal Response



SCALE 1:1

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CASE 751-07
ISSUE AK

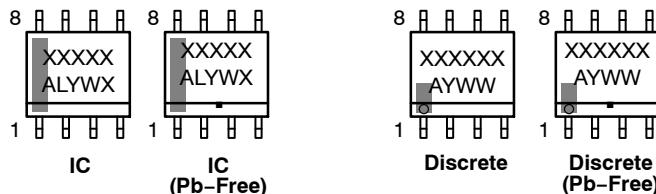
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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*

XXXXXX = Specific Device Code
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 W = Work Week
 ■ = Pb-Free Package

XXXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. Emitter 2. Collector 3. Collector 4. Emitter 5. Emitter 6. Base 7. Base 8. Emitter	STYLE 2: PIN 1. Collector, Die #1 2. Collector, #1 3. Collector, #2 4. Collector, #2 5. Base, #2 6. Emitter, #2 7. Base, #1 8. Emitter, #1	STYLE 3: PIN 1. Drain, Die #1 2. Drain, #1 3. Drain, #2 4. Drain, #2 5. Gate, #2 6. Source, #2 7. Gate, #1 8. Source, #1	STYLE 4: PIN 1. Anode 2. Anode 3. Anode 4. Anode 5. Anode 6. Anode 7. Anode 8. Common Cathode
STYLE 5: PIN 1. Drain 2. Drain 3. Drain 4. Drain 5. Gate 6. Gate 7. Source 8. Source	STYLE 6: PIN 1. Source 2. Drain 3. Drain 4. Source 5. Source 6. Gate 7. Gate 8. Source	STYLE 7: PIN 1. Input 2. External Bypass 3. Third Stage Source 4. Ground 5. Drain 6. Gate 3 7. Second Stage Vd 8. First Stage Vd	STYLE 8: PIN 1. Collector, Die #1 2. Base, #1 3. Base, #2 4. Collector, #2 5. Collector, #2 6. Emitter, #2 7. Emitter, #1 8. Collector, #1
STYLE 9: PIN 1. Emitter, Common 2. Collector, Die #1 3. Collector, Die #2 4. Emitter, Common 5. Emitter, Common 6. Base, Die #2 7. Base, Die #1 8. Emitter, Common	STYLE 10: PIN 1. Ground 2. Bias 1 3. Output 4. Ground 5. Ground 6. Bias 2 7. Input 8. Ground	STYLE 11: PIN 1. Source 1 2. Gate 1 3. Source 2 4. Gate 2 5. Drain 2 6. Drain 2 7. Drain 1 8. Drain 1	STYLE 12: PIN 1. Source 2. Source 3. Source 4. Gate 5. Drain 6. Drain 7. Drain 8. Drain
STYLE 13: PIN 1. N.C. 2. Source 3. Source 4. Gate 5. Drain 6. Drain 7. Drain 8. Drain	STYLE 14: PIN 1. N-Source 2. N-Gate 3. P-Source 4. P-Gate 5. P-Drain 6. P-Drain 7. N-Drain 8. N-Drain	STYLE 15: PIN 1. Anode 1 2. Anode 1 3. Anode 1 4. Anode 1 5. Cathode, Common 6. Cathode, Common 7. Cathode, Common 8. Cathode, Common	STYLE 16: PIN 1. Emitter, Die #1 2. Base, Die #1 3. Emitter, Die #2 4. Base, Die #2 5. Collector, Die #2 6. Collector, Die #2 7. Collector, Die #1 8. Collector, Die #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. Anode 2. Anode 3. Source 4. Gate 5. Drain 6. Drain 7. Cathode 8. Cathode	STYLE 19: PIN 1. Source 1 2. Gate 1 3. Source 2 4. Gate 2 5. Drain 2 6. Mirror 2 7. Drain 1 8. Mirror 1	STYLE 20: PIN 1. Source (N) 2. Gate (N) 3. Source (P) 4. Gate (P) 5. Drain 6. Drain 7. Drain 8. Drain
STYLE 21: PIN 1. Cathode 1 2. Cathode 2 3. Cathode 3 4. Cathode 4 5. Cathode 5 6. Common Anode 7. Common Anode 8. Cathode 6	STYLE 22: PIN 1. I/O Line 1 2. Common Cathode/VCC 3. Common Cathode/VCC 4. I/O Line 3 5. Common Anode/GND 6. I/O Line 4 7. I/O Line 5 8. Common Anode/GND	STYLE 23: PIN 1. Line 1 IN 2. Common Anode/GND 3. Common Anode/GND 4. Line 2 IN 5. Line 2 OUT 6. Common Anode/GND 7. Common Anode/GND 8. Line 1 OUT	STYLE 24: PIN 1. Base 2. Emitter 3. Collector/Anode 4. Collector/Anode 5. Cathode 6. Cathode 7. Collector/Anode 8. Collector/Anode
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. Enable 4. ILIMIT 5. Source 6. Source 7. Source 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBUCK 7. VBUCK 8. VIN
STYLE 29: PIN 1. Base, Die #1 2. Emitter, #1 3. Base, #2 4. Emitter, #2 5. Collector, #2 6. Collector, #2 7. Collector, #1 8. Collector, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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